

IR Chip--ORT008IRA

1. Scope:

- This specification applies to GaAlAs/GaAs infrared emitting diode chips

2. Structure:

- Mesa Type: rough surface.
- Electrodes:
P (Anode) Side: gold alloy.
N (Cathode) Side: gold alloy.

3. Size:

- Top Size: $170\mu\text{m} \times 170\mu\text{m} \pm 30\mu\text{m}$; Bottom Size: $200\mu\text{m} \times 200\mu\text{m} \pm 30\mu\text{m}$
- Chip Height: $215\mu\text{m} \pm 20\mu\text{m}$
- Pad Size: $100\mu\text{m} \pm 10\mu\text{m}$
- Pattern Drawing: per fig.1.

4. Electro-Optical Characteristics:

($T_a = +25^\circ\text{C}$)

Parameter	Symbol	Unit	Min	Typ	Max	Test Condition
Forward voltage	V_F	V		1.20	1.40	$I_F = 20\text{mA}$
Reverse voltage	V_R	V	5			$I_R = 10\mu\text{A}$
Peak wavelength	WLP	nm		940		$I_F = 20\text{mA}$
Radiated output Power	P_O	mw	1.0	1.2		$I_F = 20\text{mA}$

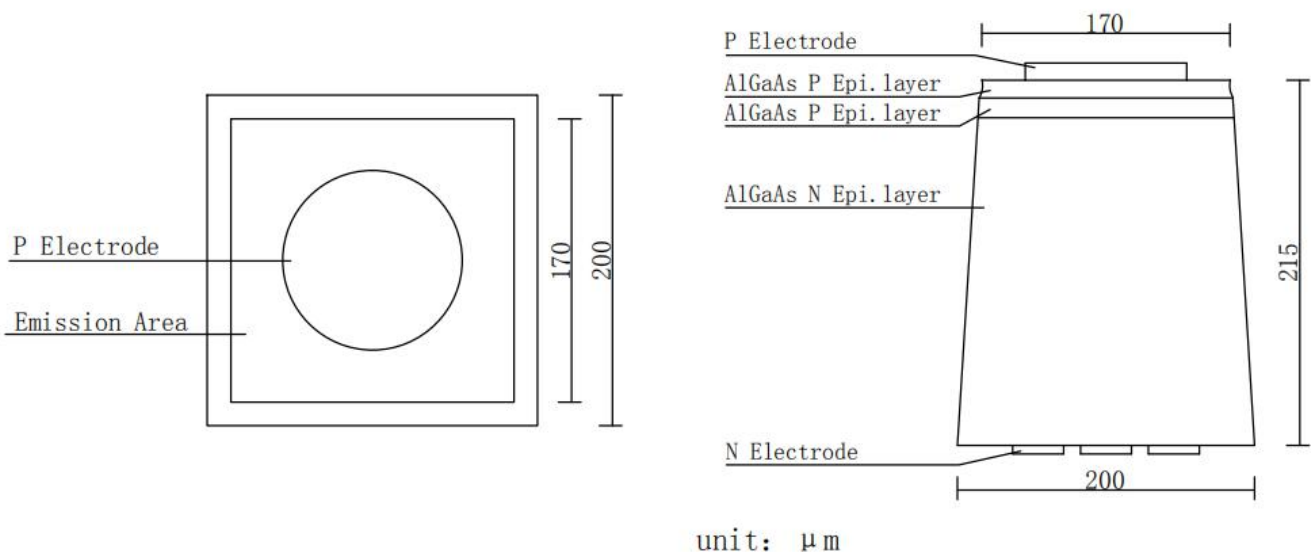


fig.1

5. Applications:

- Infrared emitter
- Common remote control system

6. Packing and Labeling:



- Packing: Sheet Type
- Each pellet is mounted on an adhesive sheet with wire-bonded electrode side up.
- Labeling: Each lot has a label sheet、 writing Type、 Lot No、 Pcs、 Avg P₀、 V_F 、 Wlp and quantity of good chips.

7. Application Notes:

- All data are measured by Orient' s tester on bare chips within 98% of the nominal value.
- Measurement error for dominant wavelength and peak wavelength is $\pm 5\text{nm}$